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Silicon NPN Power Transistors 2SD1414

DESCRIPTION

- With TO-220Fa package
- High DC current gain
- Low saturation voltage
- Complement to type 2SB1024
- DARLINGTON

APPLICATIONS

- Power amplifier and switching applications
- Hammer drive,pulse motor drive applications

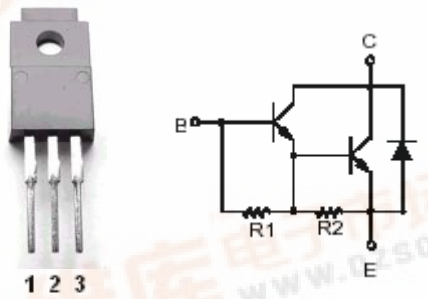

Fig.1 simplified outline (TO-220Fa) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector -emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		4	A
I_B	Base current		0.5	A
P_C	Collector power dissipation	T_C=25℃	20	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA; I_B=0	80			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=3A ;I_B=6mA			1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=3A ;I_B=6mA			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=100V; I_E=0			20	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			2.5	mA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=2V	2000			
h_{FE-2}	DC current gain	I_C=3A ; V_{CE}=2V	1000			

Switching times

t_{on}	Turn-on time	I_{B1}=-I_{B2}=6mA V_{CC}=30V ,R_L=10Ω		0.2		μs
t_{stg}	Storage time			1.5		μs
t_f	Fall time			0.6		μs

PACKAGE OUTLINE

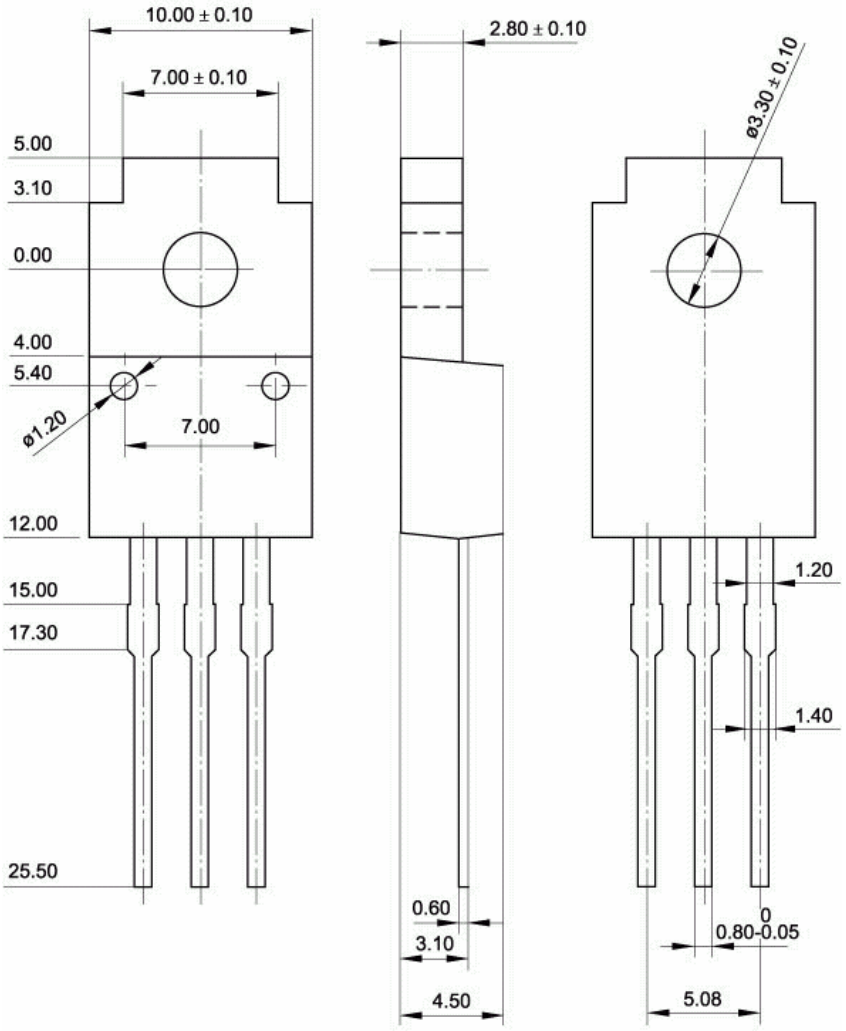

Fig.2 Outline dimensions (unindicated tolerance:±0.15 mm)